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| Journal Name: | Physical Science International Journal |
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| Manuscript Number: | 2015_PSIJ_18362 |
| Title of the Manuscript: | Diffusion and trapping of positrons in unimplanted and ion-implanted 3C-SiC and 6H-SiC |
| Type of the Article | Original Research Article |

General guideline for Peer Review process:

This journal's peer review policy states that \underline{NO} manuscript should be rejected only on the basis of 'lack of Novelty', provided the manuscript is scientifically robust and technically sound.

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PART 1: Review Comments

| Compulsory REVISION comments | Reviewer's comment | Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here) |
|------------------------------|--|---|
| Minor REVISION comments | It is necessary to add in the Introduction session two references on the papers, where SiC materials were explored using positron annihilation (materials, implanted by Al- ions with five different energies). The authors found there the forming of divacancies with lifetime equal to 218 and 216 ps etc. The references: 1. Trifthauser W. in Proc. Of the Intern. Workshop on Advanced Techniques of Positron Beam Generation and Control JAERI, Japan, 1998, p. 57. 2. A.D. Pogrebnjak, A.G. Ponomarev, A.P. Shpak, Yu.A. Kunitskii. Application of micro-nanoprobes to the analysis of small-size 3D materials, nanosystems and nanoobjects. Phys. Uspekhi 55 (3), 270 – 300, 2012. | |
| Optional/General comments | General level of the paper is rather good. It can be published in the Journal with minor corrections. | |

Reviewer Details:

| Name: | Alexander D. Pogrebnjak |
|----------------------------------|--|
| Department, University & Country | Department of Nanoelecronics, Sumy State University, Ukraine |